## **DESCRIPTION**

The AM2318 is available in SOT-23 package.

## ORDERING INFORMATION

| Package Type                            | Part Number             |            |  |  |  |  |
|---|-------------------------|------------|--|--|--|--|
| SOT-23                                  | E3                      | AM2318E3R  |  |  |  |  |
|   |                         | AM2318E3VR |  |  |  |  |
| Note                                    | V: Halogen free Package |            |  |  |  |  |
|   | R: Tape & Reel          |            |  |  |  |  |
|   | SPQ: 3,000pcs / Reel    |            |  |  |  |  |
| AiT provides all RoHS products          |                         |            |  |  |  |  |
| Suffix " V " means Halogen free Package |                         |            |  |  |  |  |

## **FEATURES**

20V / 2.0A,

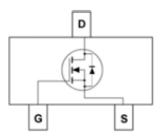
 $R_{DS(ON)}$ = 80m $\Omega(MAX)$  @V<sub>GS</sub> = 4.5V  $R_{DS(ON)}$ =90m $\Omega(MAX)$  @  $V_{GS}$  = 2.5V

- Super High dense cell design for extremely low  $R_{DS(ON)}$ .
- Reliable and Rugged.
- Available in SOT-23 Package

# **APPLICATION**

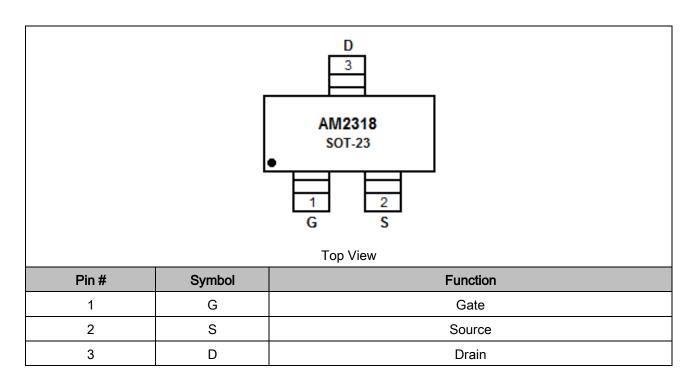
- **Power Management**
- Portable Equipment and Battery Power Systems.

# PIN DESCRIPTION





## PIN DESCRIPTION



## ABSOLUTE MAXIMUM RATINGS

#### T<sub>A</sub>=25°C, unless otherwise noted

| 1A 20               | o, anicos otherwise notes |      |
|---------------------|---------------------------|------|
| V <sub>DS</sub> , I | Drain-Source Voltage      | 20V  |
| V <sub>GS</sub> , 0 | Gate-Source Voltage       | ±8V  |
| I <sub>D</sub> , Dr | rain Current-Continuous   | 2.0A |

Stress beyond above listed "Absolute Maximum Ratings" may lead permanent damage to the device. These are stress ratings only and operations of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

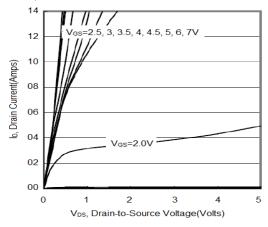
# **ELECTRICAL CHARACTERISTICS**

T<sub>A</sub>=25°C, unless otherwise noted

| Parameter                          | Symbol              | Conditions  | Min. | Тур. | Max. | Unit |  |  |
|------------------------------------|---------------------|---|------|------|------|------|--|--|
| Off Characteristics                |                     |   |      |      |      |      |  |  |
| Drain-Source Breakdown Voltage     | BV <sub>DSS</sub>   | $V_{GS} = 0V, I_D = 250uA$                                  | 20   |      |      | ٧    |  |  |
| Zero-Gate Voltage Drain Current    | I <sub>DSS</sub>    | V <sub>DS</sub> = 12V, V <sub>GS</sub> = 0V                 |      |      | 1    | uA   |  |  |
| Gate Body Leakage Current, Forward | $I_{GSSF}$          | $V_{GS}$ = 8V, $V_{DS}$ = 0V                                |      |      | 100  | nA   |  |  |
| Gate Body Leakage Current, Reverse | IGSSR               | V <sub>GS</sub> = -8V, V <sub>DS</sub> = 0V                 |      |      | -100 | nA   |  |  |
| On Characteristics                 |                     |   |      |      |      |      |  |  |
| Gate Threshold Voltage             | $V_{\text{GS(th)}}$ | $V_{GS}=V_{DS}$ , $I_D=250uA$                               | 0.4  |      | 1.3  | ٧    |  |  |
| Static Drain-Source On-Resistance  | Rds(on)             | $V_{GS}$ = 4.5V, $I_{D}$ = 3.6A                             |      | 70   | 80   | mΩ   |  |  |
|                                    |                     | $V_{GS} = 2.5V, I_D = 3.1A$                                 |      | 75   | 90   |      |  |  |
| Source-Drain Diode                 |                     |   |      |      |      |      |  |  |
| Drain-Source Diode Forward Voltage | V <sub>SD</sub>     | $V_{GS} = 0V, I_S = 0.94A$                                  |      |      | 1.2  | V    |  |  |
| Switching Characteristics          |                     |   |      |      |      |      |  |  |
| Turn-On Delay Time                 | t <sub>d(on)</sub>  | $V_{DD} = 10V, I_D = 1A,$<br>$V_{GS} = 4.5V, R_G = 6\Omega$ |      | 5    | 15   | ns   |  |  |
| Turn-On Rise Time                  | tr                  |   |      | 8.5  | 17   | ns   |  |  |
| Turn-Off Delay Time                | $t_{\text{d(off)}}$ |   |      | 11   | 20   | ns   |  |  |
| Turn-Off Fall Time                 | tf                  |   |      | 3    | 10   | ns   |  |  |
| Total Gate Charge                  | Qg                  | $V_{DS} = 10V, I_D = 1.7A,$<br>$V_{GS} = 4.5V$              |      | 3.5  | 5    | nC   |  |  |
| Gate-Source Charge                 | Q <sub>gs</sub>     |   |      | 0.55 |      | nC   |  |  |
| Gate-Drain Charge                  | $Q_{gd}$            |   |      | 0.95 |      | nC   |  |  |

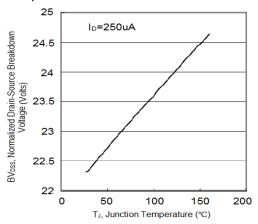
### TYPICAL PERFORMANCE CHARACTERISTICS

#### 1. Output Characteristics

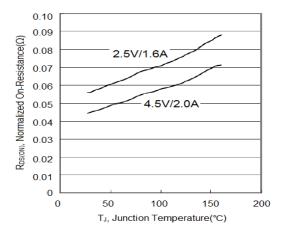


## 3. Breakdown Voltage Variation with

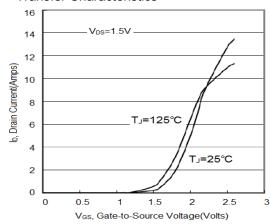
#### Temperature



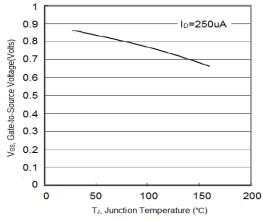
### 5. On-Resistance Variation with Temperature



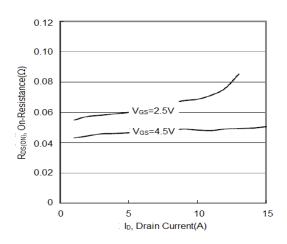
#### 2. Transfer Characteristics



#### 4. Gate Threshold Variation with Temperature

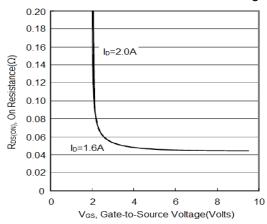


### 6. On-Resistance vs. Drain Current

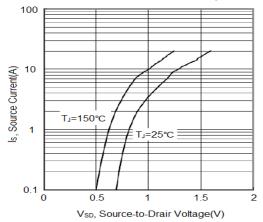




#### 7. On-Resistance vs. Gate-to-Source Voltage

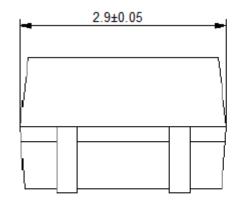


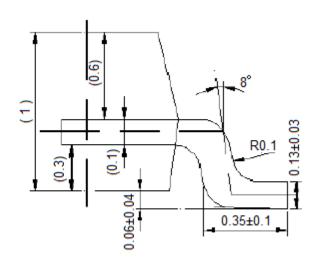
#### Source-Drain Diode Forward Voltage 8.

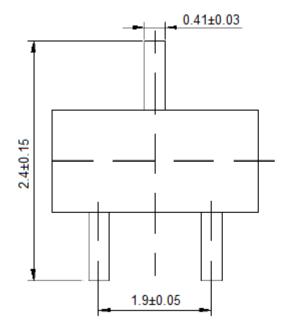


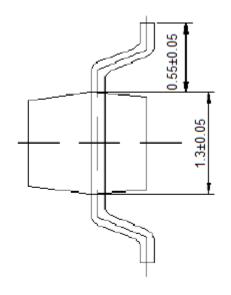
# PACKAGE INFORMATION

Dimension in SOT-23 (Unit: mm)











## IMPORTANT NOTICE

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